



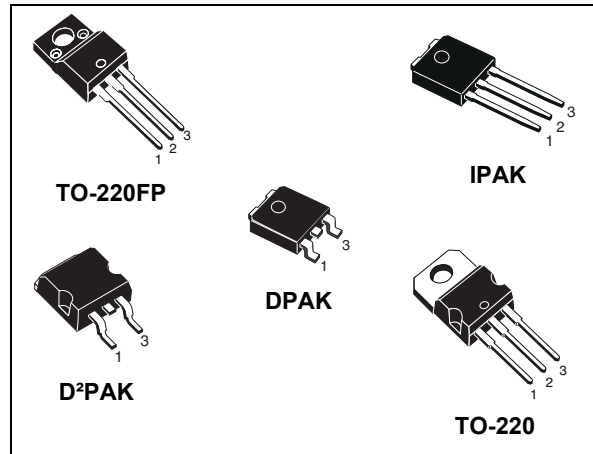
STB60N55F3 - STD60N55F3 - STF60N55F3 STP60N55F3 - STU60N55F3

N-channel 55V - 8.0mΩ - 65A - DPAK - IPAK - D²PAK - TO-220/FP
STripFET™ Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STB60N55F3	55V	<10.5mΩ	65A	110W
STD60N55F3	55V	<10.5mΩ	65A	110W
STF60N55F3	55V	<10.5mΩ	30A	30W
STP60N55F3	55V	<10.5mΩ	65A	110W
STU60N55F3	55V	<10.5mΩ	65A	110W

- Standard threshold drive
- 100% avalanche tested



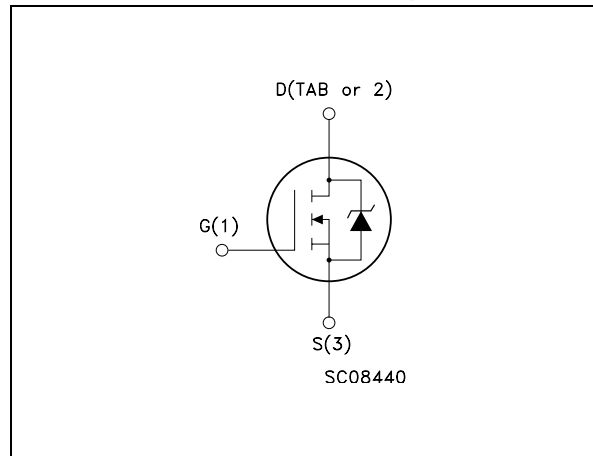
Description

This n-channel enhancement mode Power MOSFET is the latest refinement of STMicroelectronics' unique "Single Feature Size™" strip-based process, which has decreased the critical alignment steps, offering remarkable manufacturing reproducibility. The outcome is a transistor with extremely high packing density for low onresistance, rugged avalanche characteristics and low gate charge.

Applications

- Switching application

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STB60N55F3	60N55F3	D ² PAK	Tape & reel
STD60N55F3	60N55F3	DPAK	Tape & reel
STF60N55F3	60N55F3	TO-220FP	Tube
STP60N55F3	60N55F3	TO-220	Tube
STU60N55F3	60N55F3	IPAK	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK/D ² PAK TO-220/IPAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} =0)	55		V
V _{GS}	Gate-source voltage	± 20		V
I _D	Drain current (continuous) at T _C = 25°C	65	30	A
I _D	Drain current (continuous) at T _C = 100°C	46	21	A
I _{DM} ⁽¹⁾	Drain current (pulsed)	260	120	A
P _{TOT}	Total dissipation at T _C = 25°C	110	30	W
	Derating factor	0.73	0.2	W/°C
dv/dt ⁽²⁾	Peak diode recovery voltage slope	11		V/ns
E _{AS} ⁽³⁾	Single pulse avalanche energy	390		mJ
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; T _C =25°C)	--	2500	V
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 175		°C

1. Pulse width limited by safe operating area
2. I_{SD} ≤ 65A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{jmax}
3. Starting T_j=25°C, I_d=32A, V_{dd}=25V

Table 2. Thermal resistance

Symbol	Parameter	Value					Unit
		DPAK	IPAK	D ² PAK	TO-220	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	1.36			5	°C/W	
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	50	--	35	--	--	°C/W
R _{thj-a}	Thermal resistance junction-ambient max	--	100	--	62.5		°C/W
T _l	Maximum lead temperature for soldering purpose	--	275	--	300		°C

1. When mounted on FR-4 board of 1inch², 2oz Cu

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	55			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 32A$		8.0	10.5	m Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 25V, I_D = 32A$		50		S
C_{iss}	Input capacitance	$V_{DS} = 25V, f = 1MHz, V_{GS} = 0$		2200		pF
C_{oss}	Output capacitance			500		pF
C_{rss}	Reverse transfer capacitance			25		pF
Q_g	Total gate charge	$V_{DD} = 27V, I_D = 65A$		33.5	45	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10V$		12.5		nC
Q_{gd}	Gate-drain charge	(see Figure 15)		9.5		nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 27V$, $I_D = 32A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ <i>(see Figure 17)</i>		20 50		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 27V$, $I_D = 32A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ <i>(see Figure 17)</i>		35 11.5		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				65 260	A A
V_{SD}	Forward on voltage	$I_{SD} = 65A$, $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 65A$, $V_{DD} = 30V$ $di/dt = 100A/\mu s$, $T_j = 150^\circ C$ <i>(see Figure 16)</i>		47 87 3.7		ns nC A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220 D²PAK / IPAK / DPAK

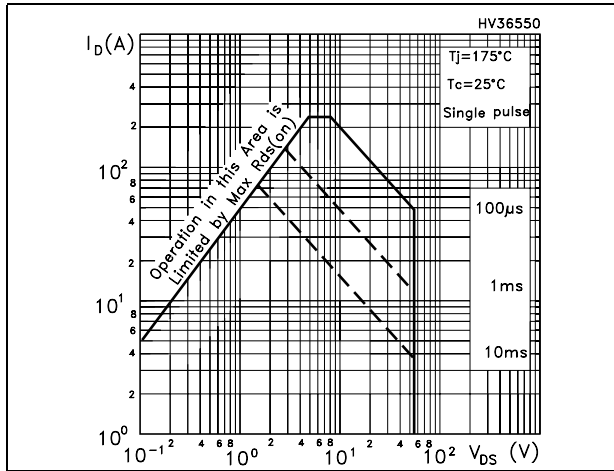


Figure 2. Thermal impedance for TO-220 D²PAK / IPAK / DPAK

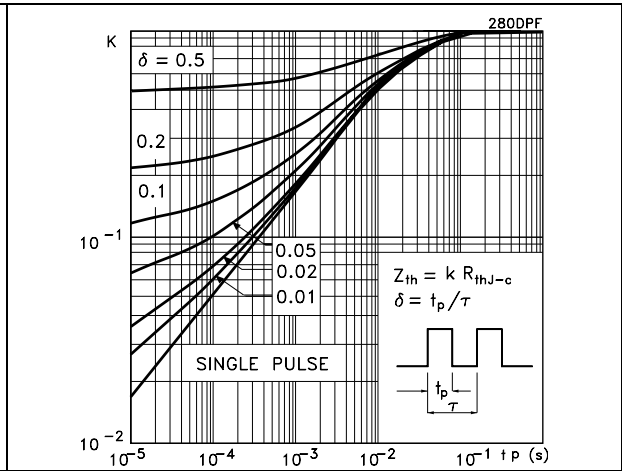


Figure 3. Safe operating area for TO-220FP

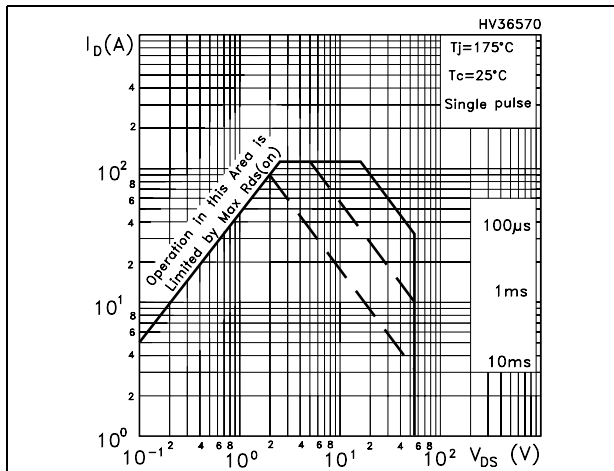


Figure 4. Thermal impedance for TO-220FP

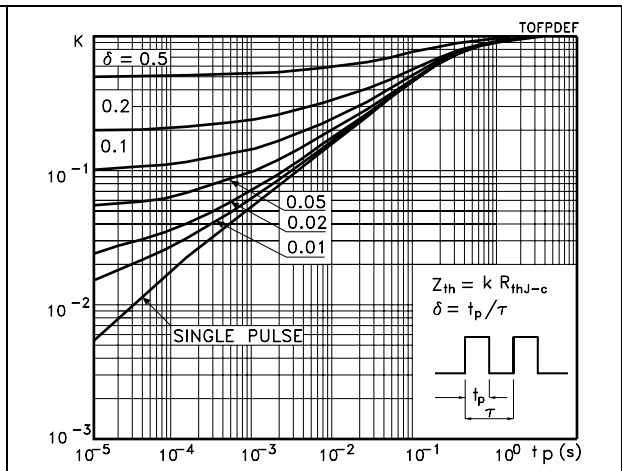


Figure 5. Output characteristics

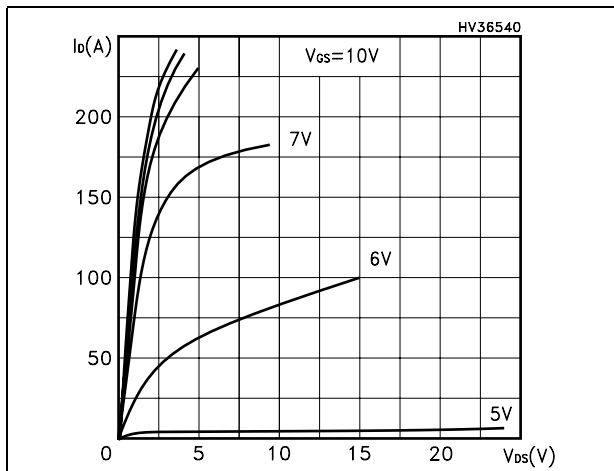


Figure 6. Transfer characteristics

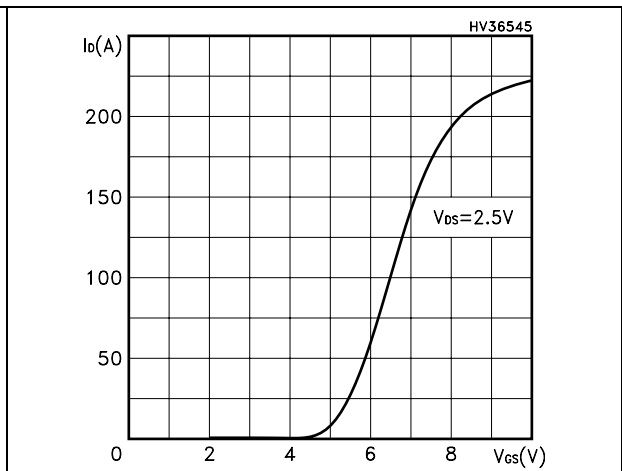


Figure 7. Normalized BV_{DSS} vs temperature Figure 8. Static drain-source on resistance

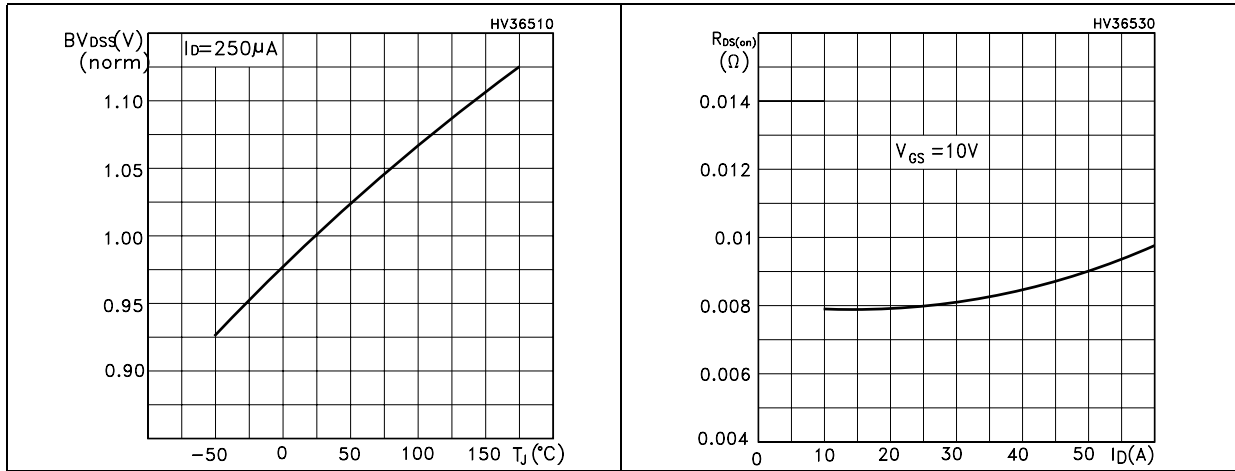


Figure 9. Gate charge vs gate-source voltage Figure 10. Capacitance variations

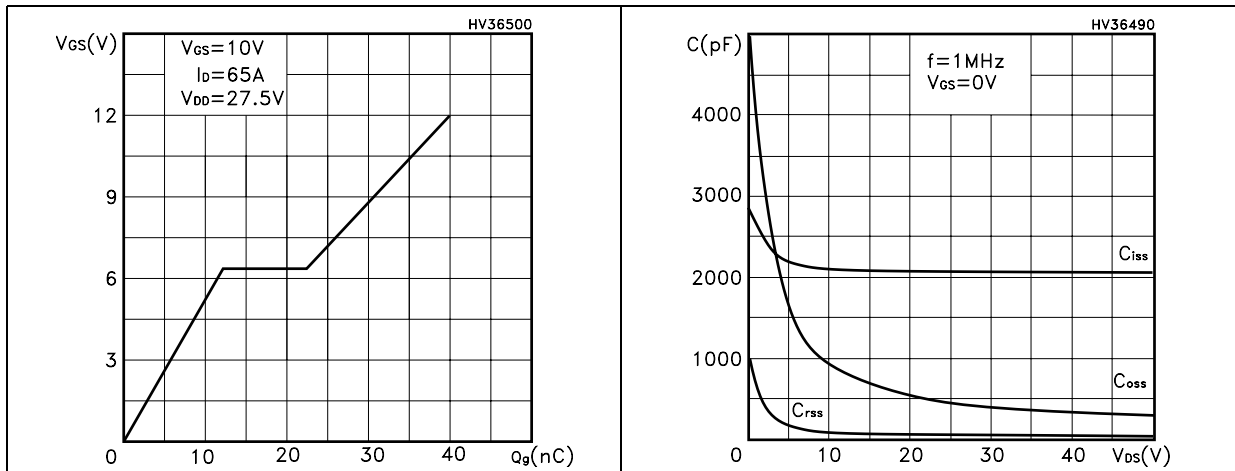


Figure 11. Normalized gate threshold voltage vs temperature Figure 12. Normalized on resistance vs temperature

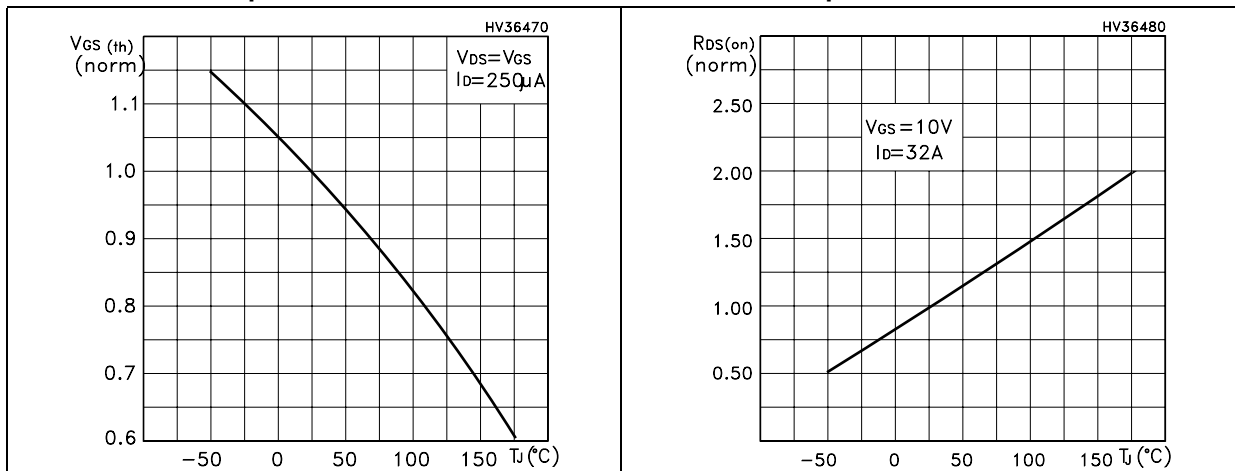
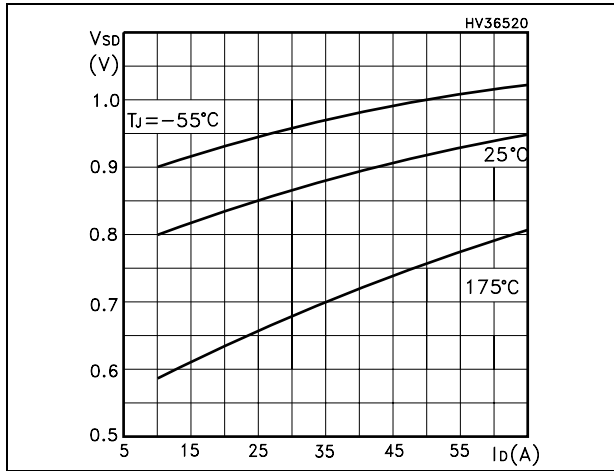


Figure 13. Source-drain diode forward characteristics



3 Test circuit

Figure 14. Switching times test circuit for resistive load

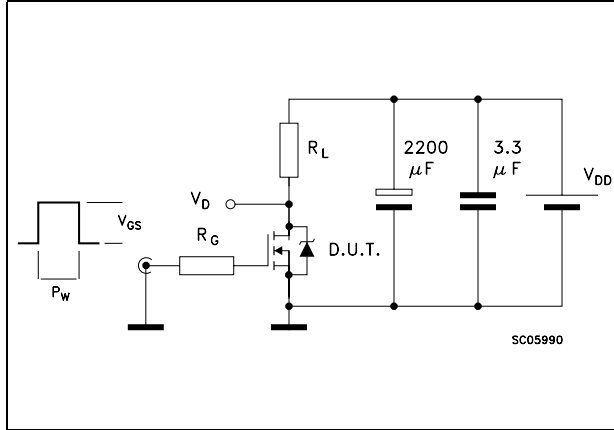


Figure 15. Gate charge test circuit

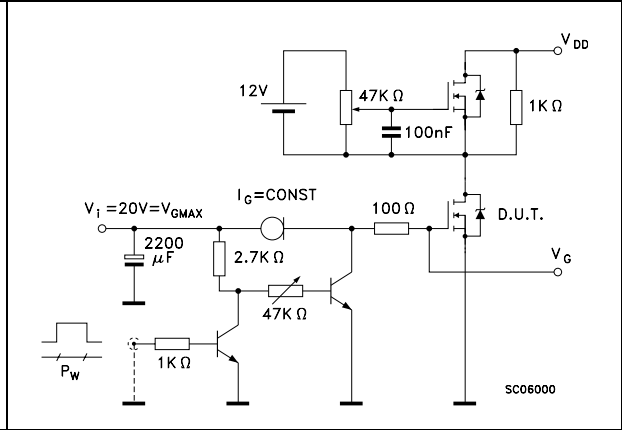


Figure 16. Test circuit for inductive load switching and diode recovery times

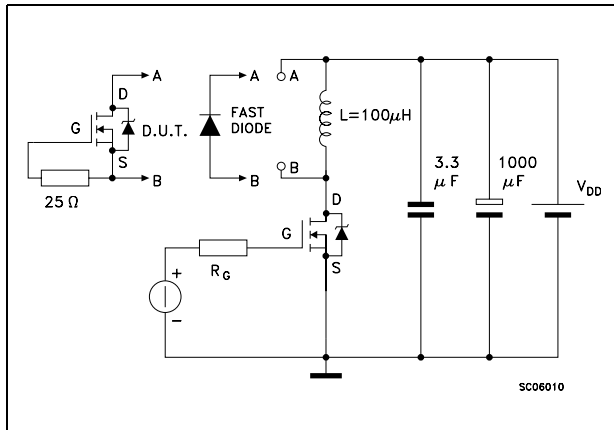


Figure 17. Unclamped Inductive load test circuit

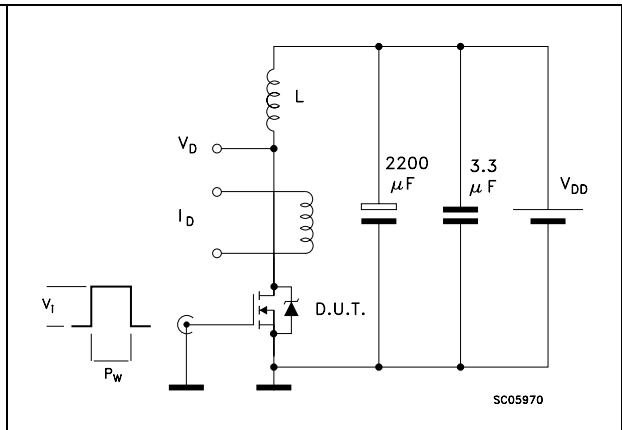


Figure 18. Unclamped inductive waveform

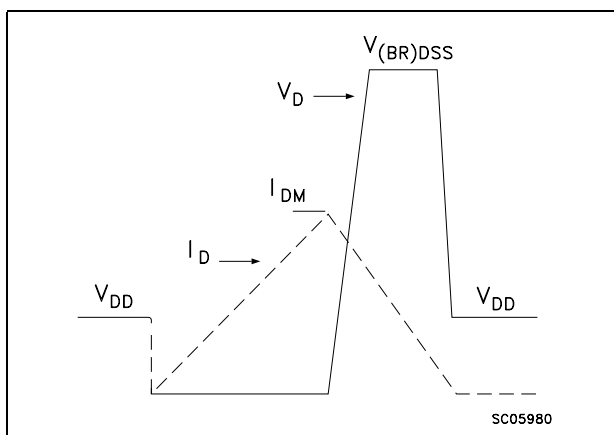
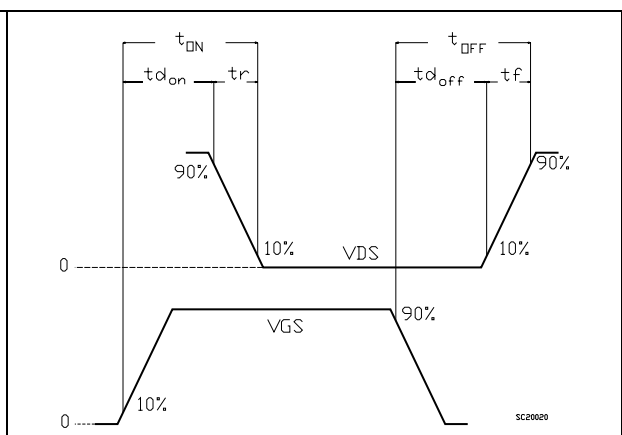


Figure 19. Switching time waveform

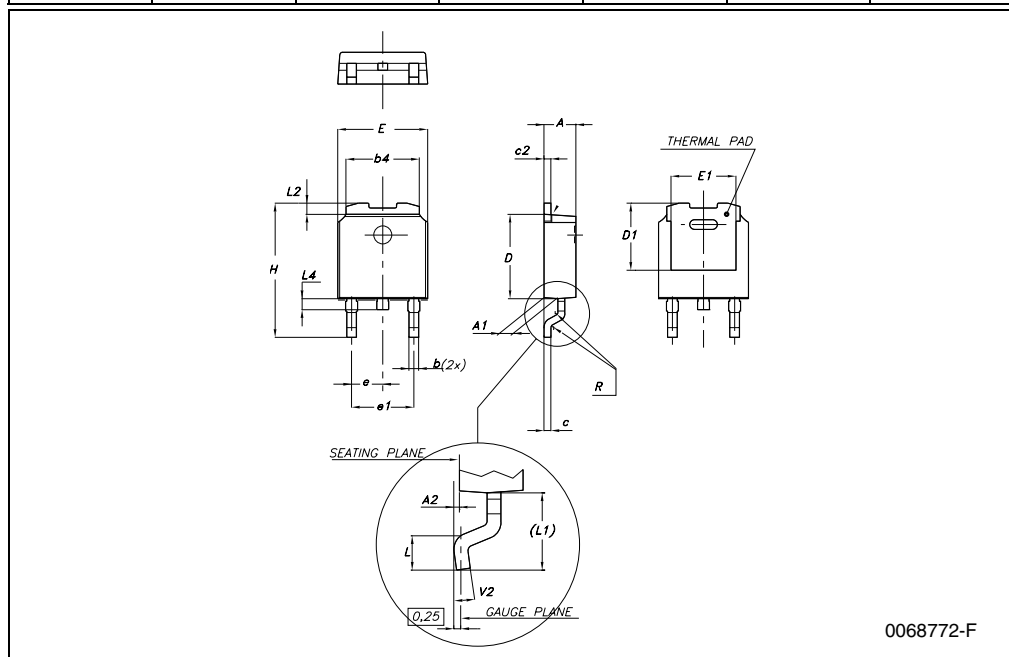


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

DPAK MECHANICAL DATA

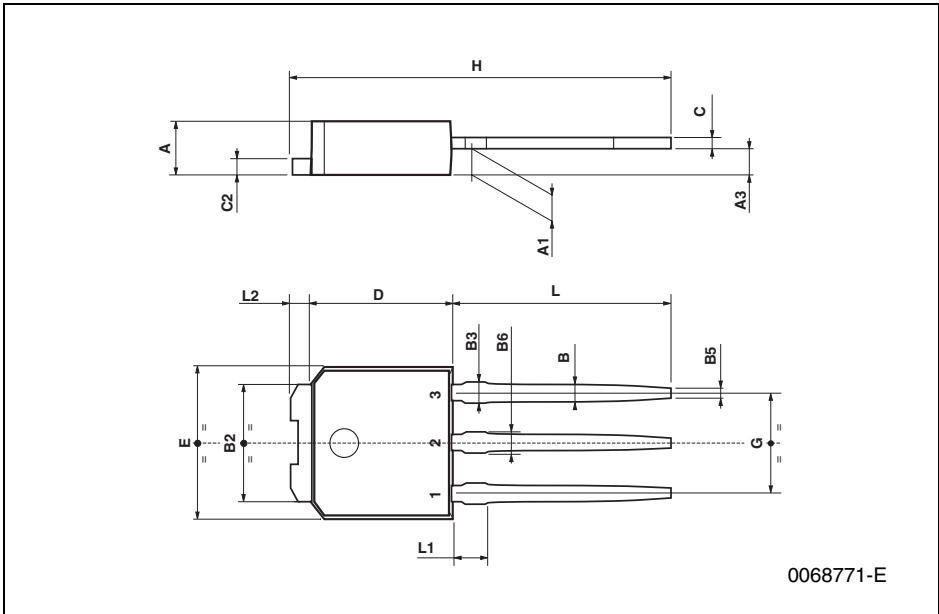
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



0068772-F

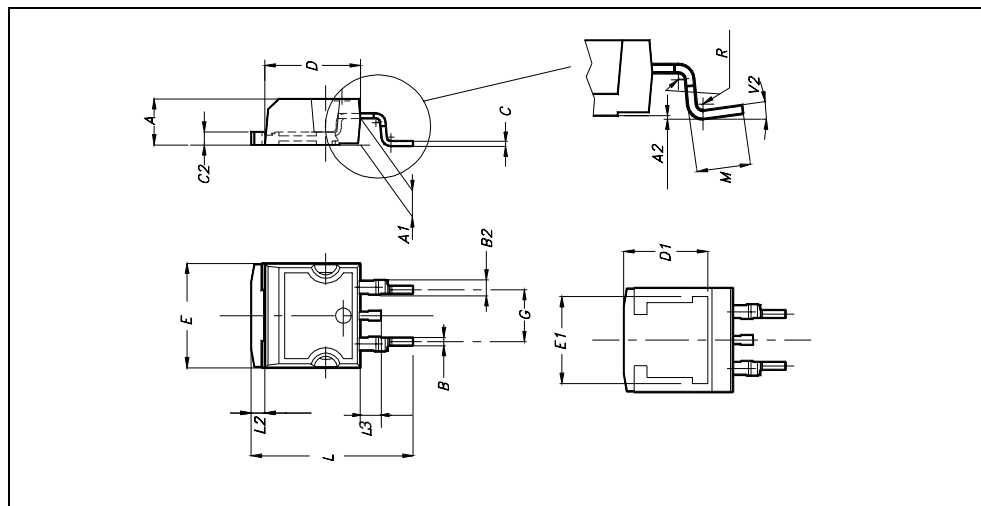
TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



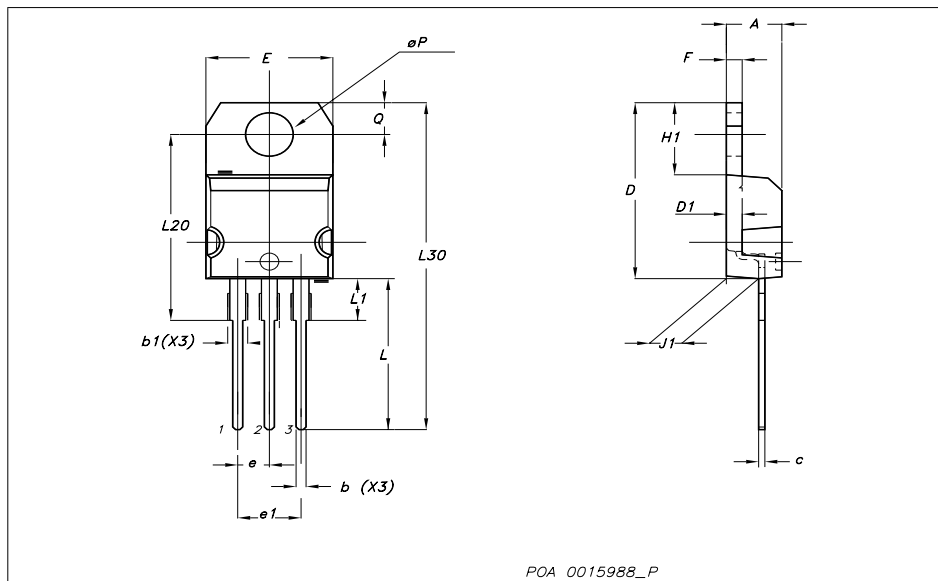
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



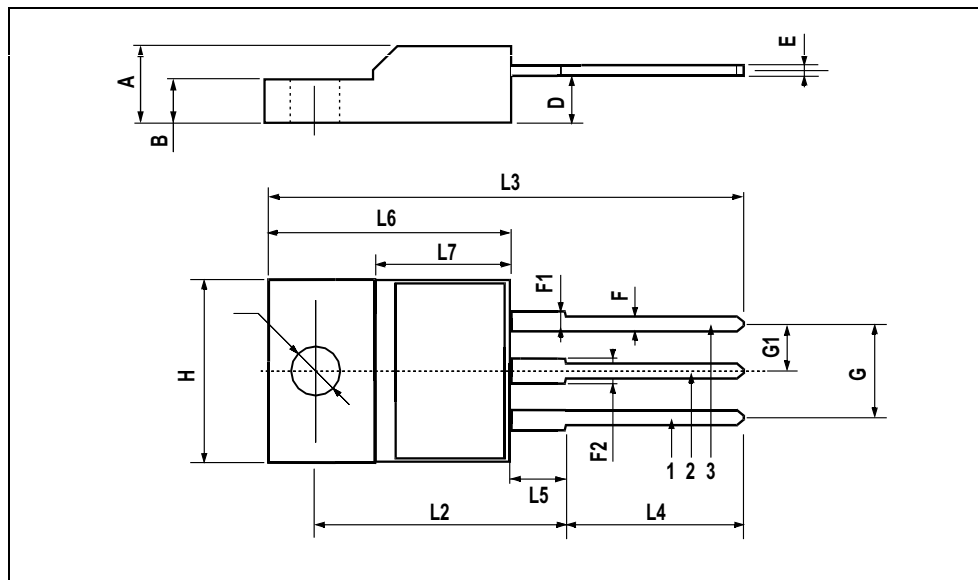
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
θP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



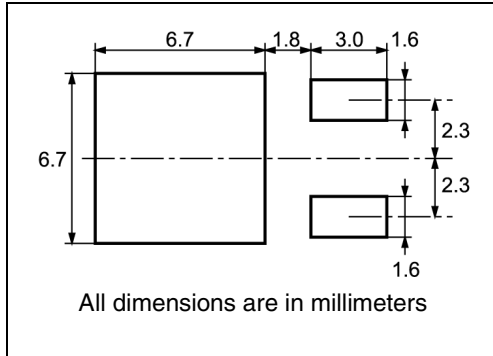
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

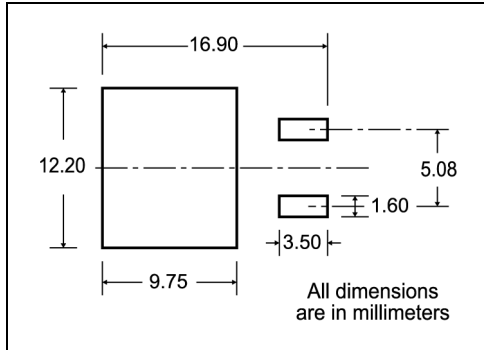
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TRL

* on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Feb-2007	1	First release
22-Feb-2007	2	Description has been updated

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